



6/3/03

1765

#21/E
ja
6/8/03

MEMC 99-0900 (2632)
PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application of Fuerhoff et al.

Art Unit 1765

Serial No. 09/502,340

Filed February 10, 2000

For METHOD AND APPARATUS FOR CONTROLLING DIAMETER OF A SILICON
CRYSTAL IN A LOCKED SEED LIFT GROWTH PROCESS

Examiner M. Anderson

June 2, 2003

RECEIVED
JUN 06 2003
TC 1700

AMENDMENT D

TO THE COMMISSIONER FOR PATENTS,

SIR:

In response to the Office action mailed April 2, 2003, please enter the following
amendments:

IN THE CLAIMS

Please amend the claims as follows:

E1
Claim 1 (currently amended): A method for use in combination with a crystal growing
apparatus for growing a monocrystalline ingot according to the Czochralski process, said crystal
growing apparatus having a heated crucible containing a semiconductor melt from which the
ingot is grown, said ingot being grown on a seed crystal pulled from the melt, said method
comprising the steps of:

defining a temperature model representative of variations in the temperature of the melt in
response to variations in power supplied to a heater for heating the melt;